



# STD85N3LH5 STP85N3LH5 - STU85N3LH5

N-channel 30 V, 0.0042  $\Omega$ , 80 A, DPAK, TO-220, IPAK  
STripFET™ V Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STD85N3LH5	30 V	< 0.005 $\Omega$	80 A
STP85N3LH5	30 V	< 0.0054 $\Omega$	80 A
STU85N3LH5	30 V	< 0.0054 $\Omega$	80 A

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- High avalanche ruggedness
- Low gate drive power losses

## Application

- Switching applications

## Description

This product utilizes the 5<sup>th</sup> generation of design rules of ST's proprietary STripFET™ technology. The lowest available R<sub>DS(on)</sub> \* Q<sub>g</sub>, in the standard packages, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.

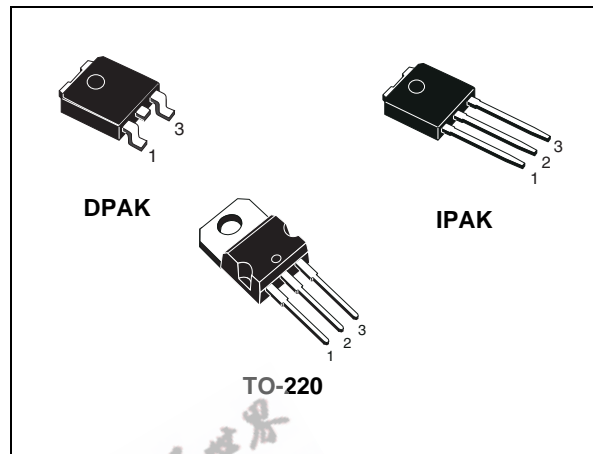


Figure 1. Internal schematic diagram

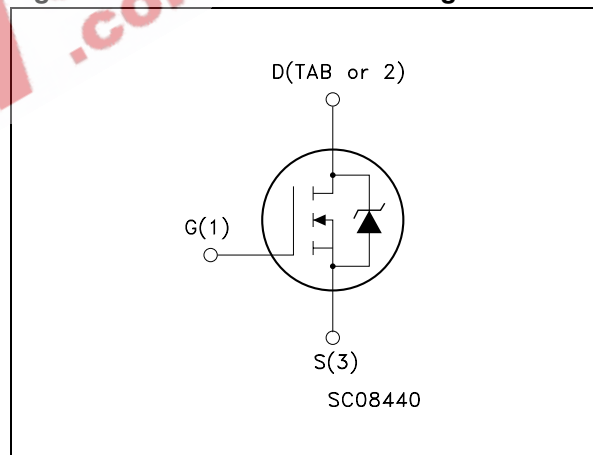


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD85N3LH5	85N3LH5	DPAK	Tape and reel
STP85N3LH5	85N3LH5	TO-220	Tube
STU85N3LH5	85N3LH5	IPAK	Tube

# Contents

1	<b>Electrical ratings</b> .....	3
2	<b>Electrical characteristics</b> .....	4
2.1	Electrical characteristics (curves) .....	6
3	<b>Test circuit</b> .....	8
4	<b>Package mechanical data</b> .....	10
5	<b>Packaging mechanical data</b> .....	13
6	<b>Revision history</b> .....	14



# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ ) @ $T_{JMAX}$	35	V
$V_{GS}$	Gate-source voltage	$\pm 22$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	55	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
	Derating factor	0.47	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	165	mJ
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	175	$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 40\text{ A}$ ,  $V_{DD} = 25\text{ V}$

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.14	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-case max	100	$^\circ\text{C/W}$
$T_j$	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 20\text{ V}$ $V_{DS} = 20\text{ V}$ , $T_c = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 22\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$ SMD version		0.042	0.005	$\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$		0.0046	0.0054	$\Omega$
		$V_{GS} = 5\text{ V}$ , $I_D = 40\text{ A}$ SMD version		0.0052	0.0065	$\Omega$
		$V_{GS} = 5\text{ V}$ , $I_D = 40\text{ A}$		0.0058	0.0071	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$		1850		pF
$C_{oss}$	Output capacitance			380		pF
$C_{rss}$	Reverse transfer capacitance			58		pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}$ , $I_D = 80\text{ A}$		14		nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 5\text{ V}$		6.8		nC
$Q_{gd}$	Gate-drain charge	(see Figure 16)		4.7		nC
$Q_{gs1}$	Pre $V_{th}$ gate-to-source charge	$V_{DD} = 15\text{ V}$ , $I_D = 80\text{ A}$		2.3		nC
$Q_{gs2}$	Post $V_{th}$ gate-to-source charge	$V_{GS} = 5\text{ V}$ (see Figure 19)		4.5		nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain		1.2		$\Omega$

**Table 6. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 15\text{ V}$ , $I_D = 40\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 5\text{ V}$ <i>(see Figure 15)</i>		6 14		ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD} = 15\text{ V}$ , $I_D = 40\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 5\text{ V}$ <i>(see Figure 15)</i>		23.6 10.8		ns ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$ , $V_{GS} = 0$			1.1	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 20\text{ V}$ <i>(see Figure 17)</i>		31.8 26.1 1.6		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

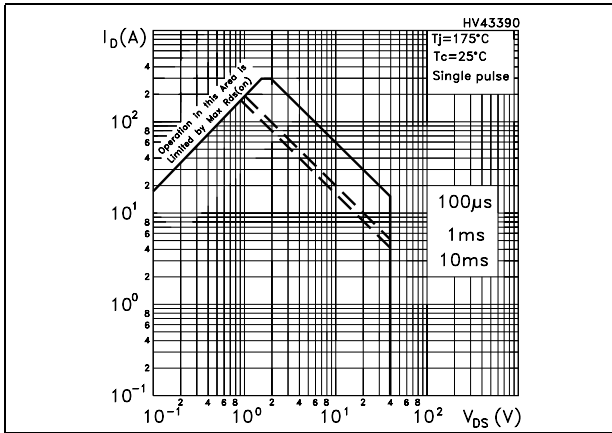


Figure 3. Thermal impedance

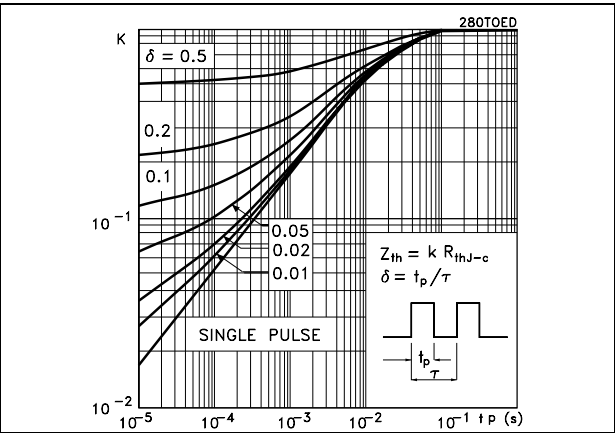


Figure 4. Output characteristics

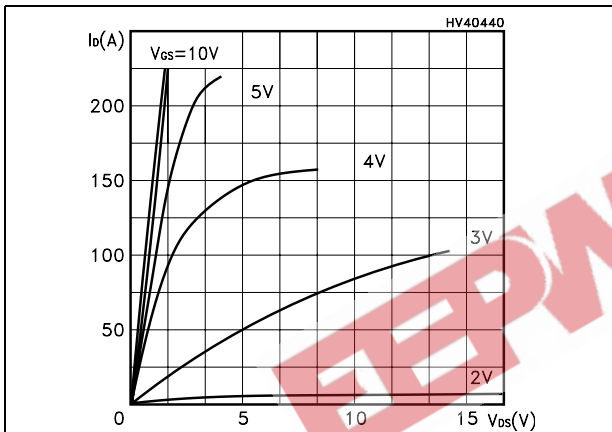


Figure 5. Transfer characteristics

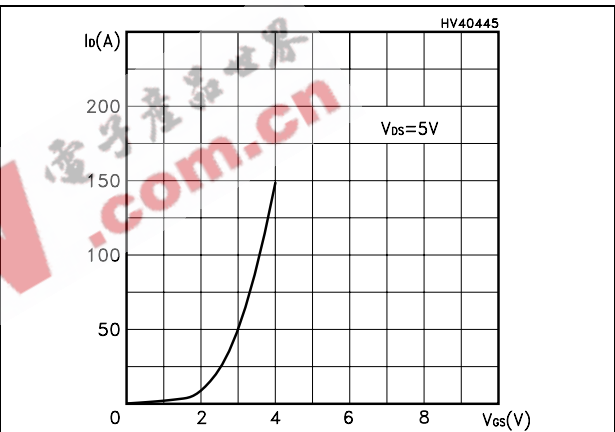


Figure 6. Normalized  $B_{V_{DS}}$  vs temperature

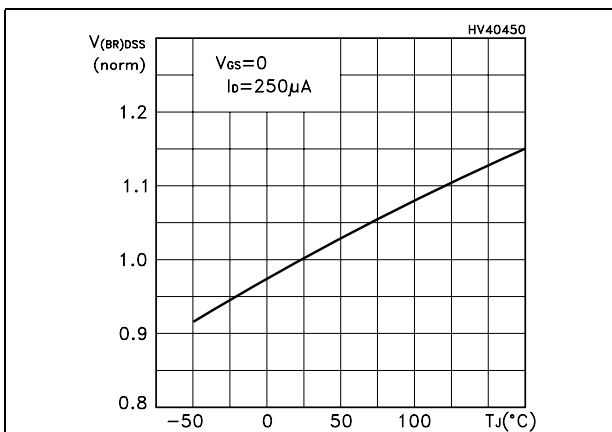


Figure 7. Static drain-source on resistance

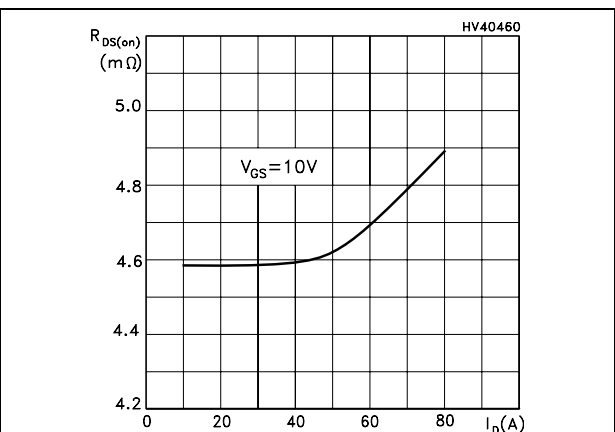


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

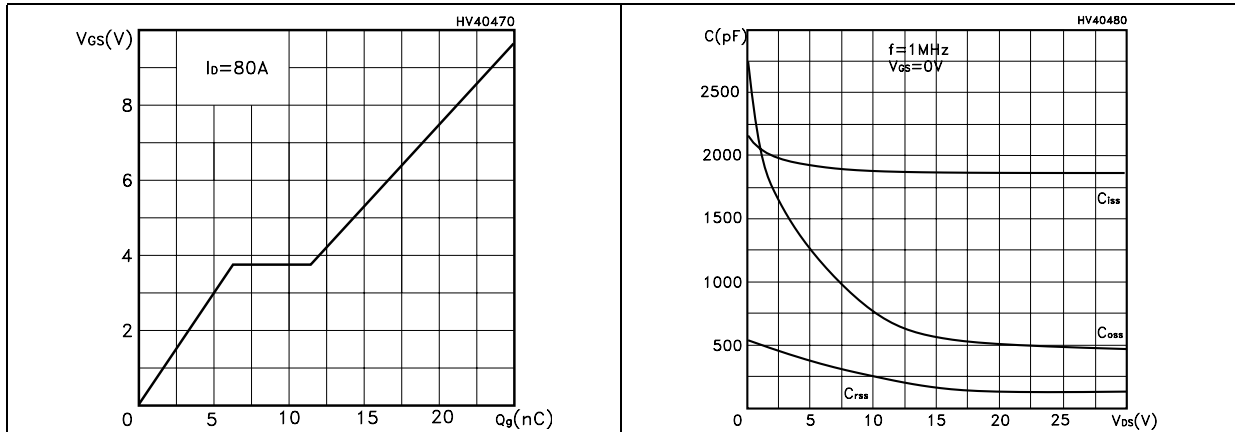


Figure 10. Normalized gate threshold voltage vs temperature

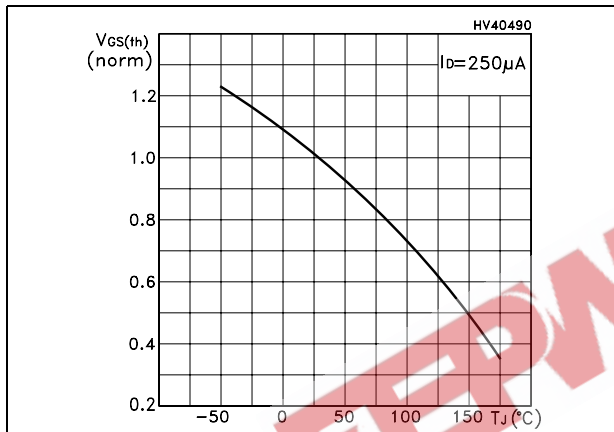


Figure 11. Normalized on resistance vs temperature

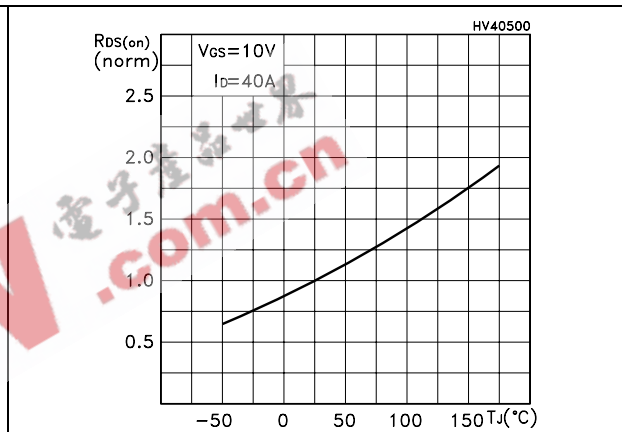
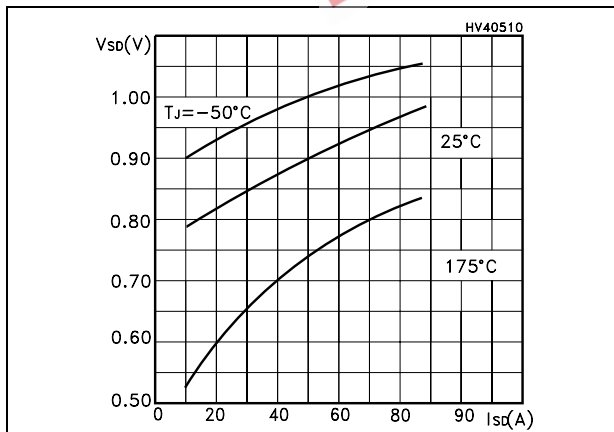


Figure 12. Source-drain diode forward characteristics



### 3 Test circuit

Figure 13. Unclamped inductive load test circuit

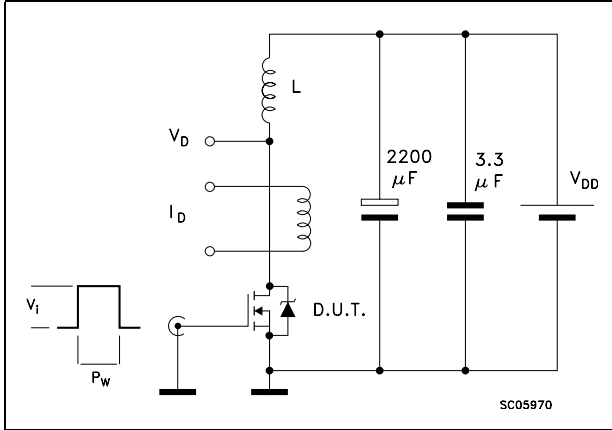


Figure 14. Unclamped inductive waveform

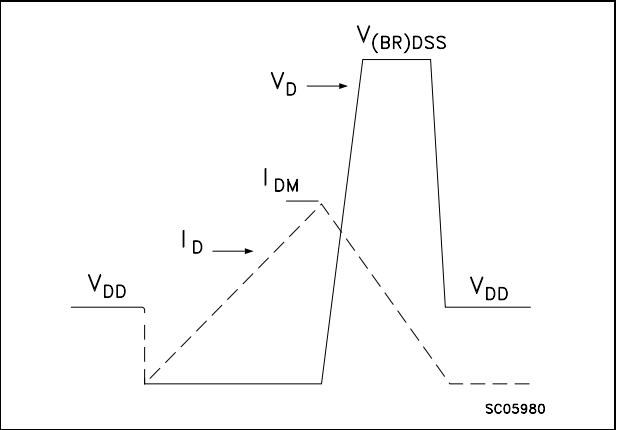


Figure 15. Switching times test circuit for resistive load

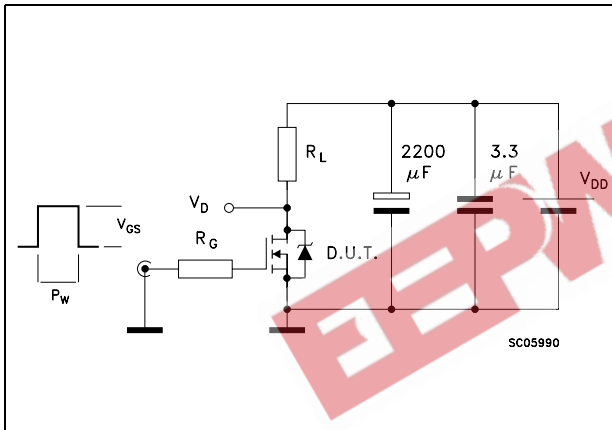


Figure 16. Gate charge test circuit

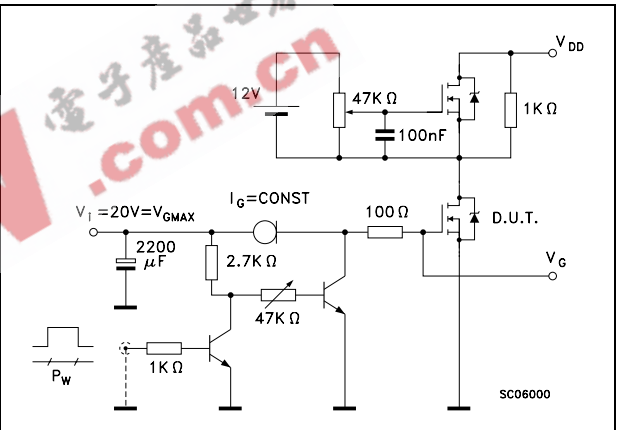


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Switching time waveform

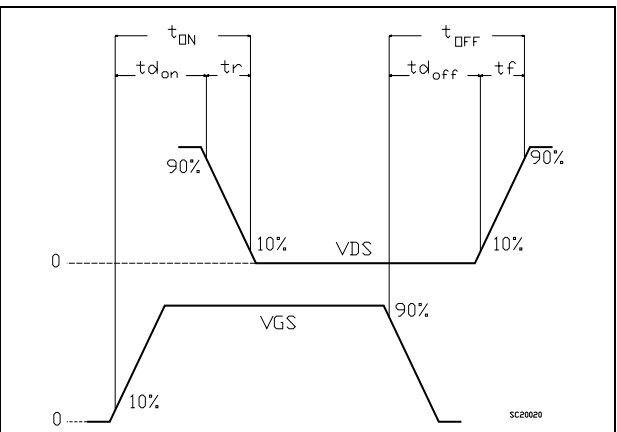
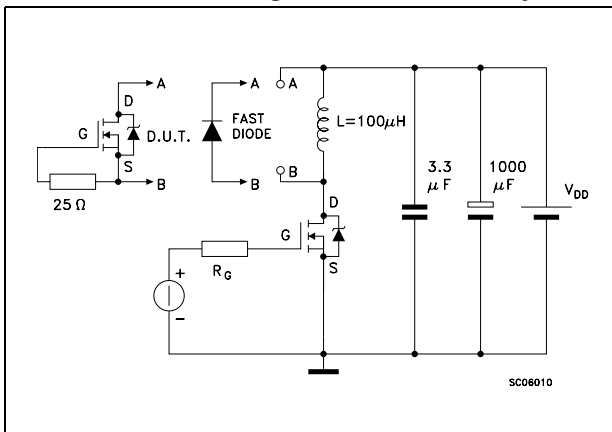
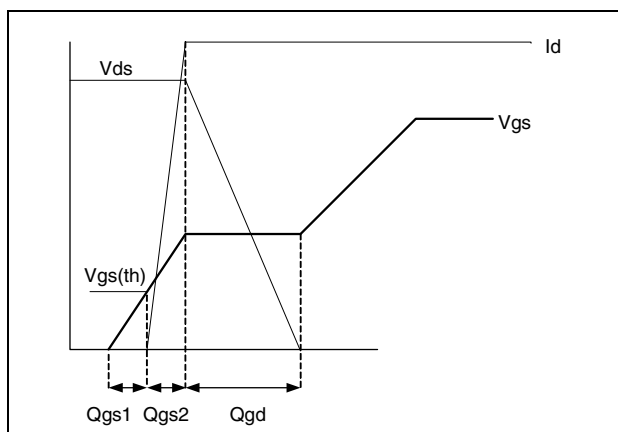




Figure 19. Gate charge waveform



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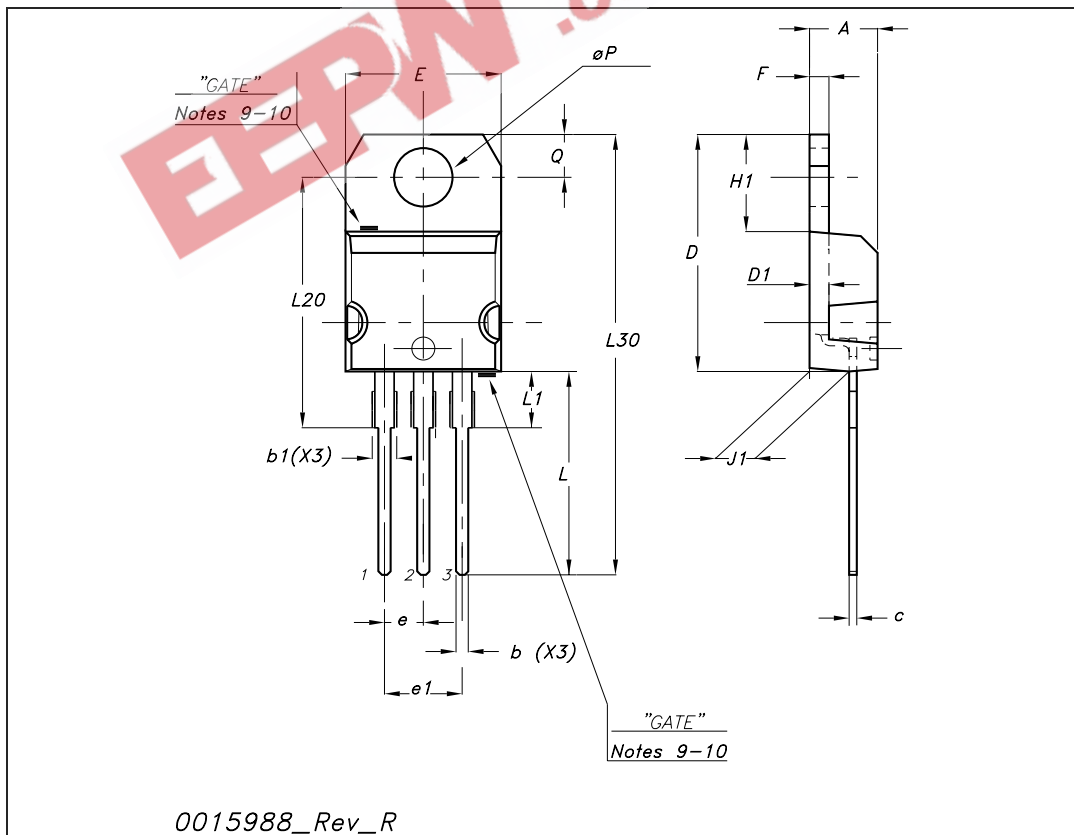
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

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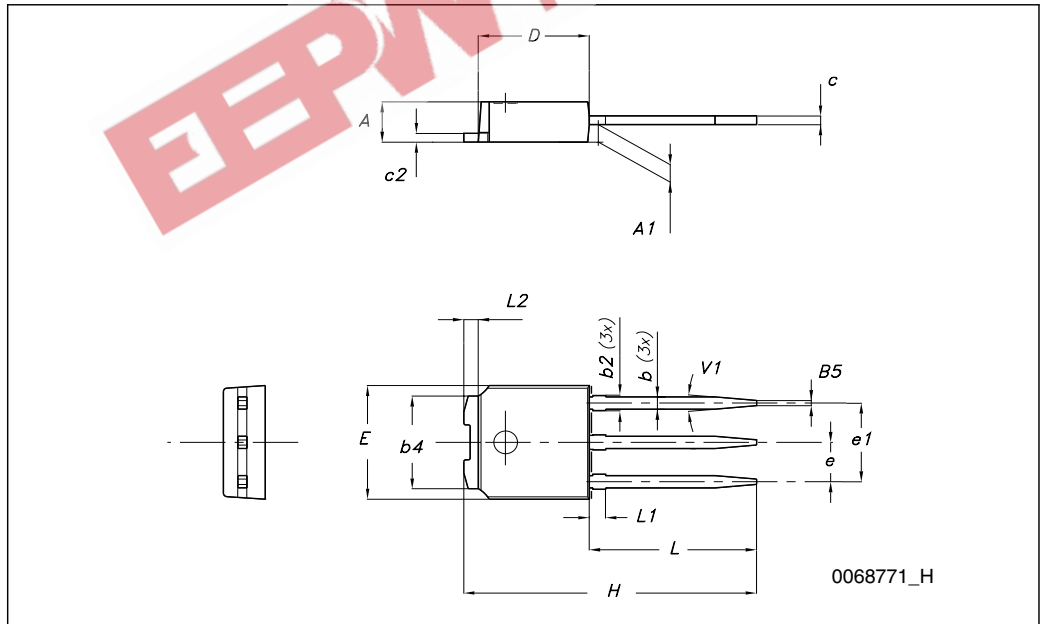
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



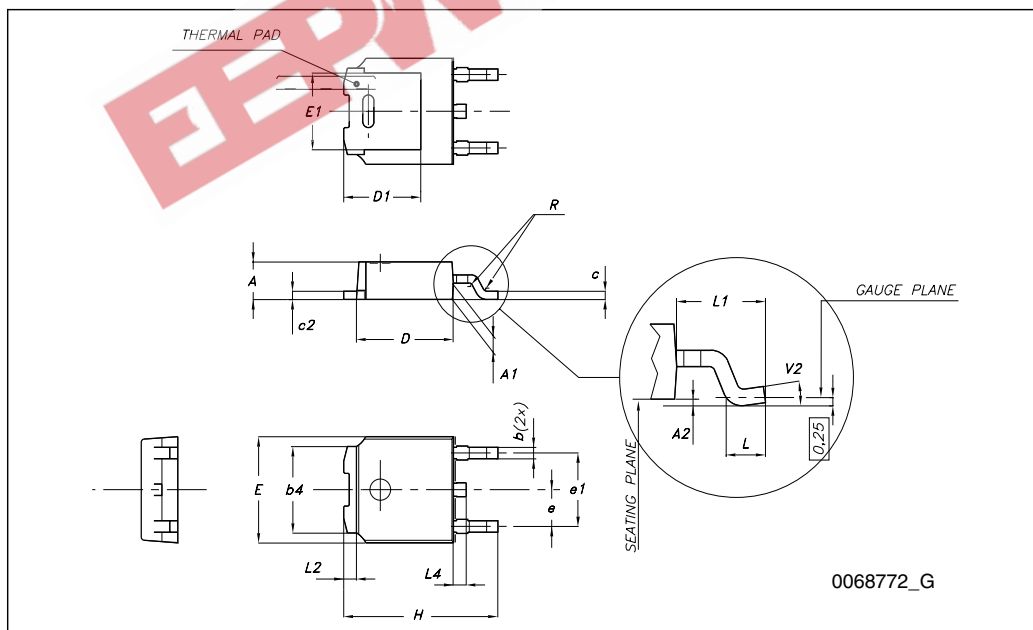
**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



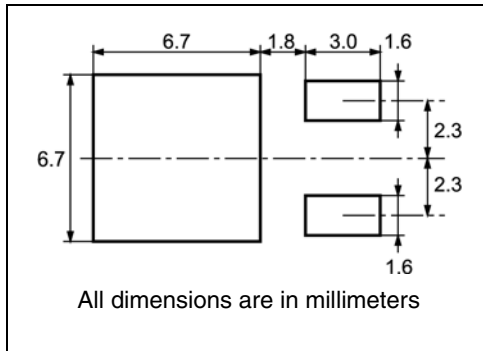
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



## 5 Packaging mechanical data

### DPAK FOOTPRINT



### TAPE AND REEL SHIPMENT

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

## 6 Revision history

Table 8. Document revision history

Date	Revision	Changes
19-Oct-2007	1	First release
20-Feb-2008	2	Minor text changes to improve readability
21-Jul-2008	3	<ul style="list-style-type: none"><li>– Added new package, mechanical data: TO-220</li><li>– <a href="#">Figure 2: Safe operating area</a> has been corrected</li><li>– <a href="#">Figure 7: Static drain-source on resistance</a> updated</li><li>– New value on <a href="#">Table 2: Absolute maximum ratings</a></li></ul>
20-Aug-2008	4	Added max value on $V_{GS(th)}$ ( <a href="#">Table 4</a> )
25-Sep-2008	5	$V_{GS}$ values has been changed on <a href="#">Table 2</a> and <a href="#">Table 4</a>

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